Elektronische Bauelemente

SD106WS

200 mA, 30 V

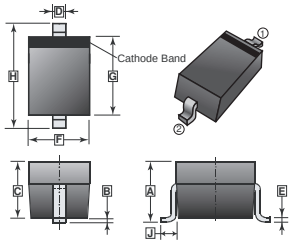
Plastic-Encapsulate Fast Schottky Diode

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS device, steering, Biasing, and coupling diodes for fast switching and Low logic level applications.

SOD-323



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.05 REF.		E	0.080	0.180
B	0.20 REF.		F	1.15	1.45
C	0.80	1.00	G	1.60	1.80
D	0.25	0.40	H	2.30	2.70

MARKING : S21

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS, Single Diode at T_A = 25℃

PARAMETER	SYMBOL	RATINGS	UNIT
Non-Repetitive Peak reverse voltage	V_{RM}	30	V
Forward Current	I_{FM}	200	mA
Forward Surge Current (t_P =10ms)	I_{FSM}	1	A
Power Dissipation (T_C=25℃)	P_{TOT}	250	mW
Thermal Resistance Junction to Ambient Air	$T_{\theta JA}$	500	℃/W
Junction, Storage Temperature	T_J, T_{STG}	150, -65~150	℃

ELECTRICAL RATING at T_A = 25℃

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Reverse Breakdown Voltage	V_R	30			V	I_R = 100μA
Forward Voltage	V_F		260		mV	I_F =2mA
			320			I_F =15mA
			420			I_F =100mA
			490	550		I_F =200mA
Reverse Current	I_R			5	μA	V_R = 30V
Capacitance between Terminals	C_T			15	pF	V_R = 10V, f = 1MHZ

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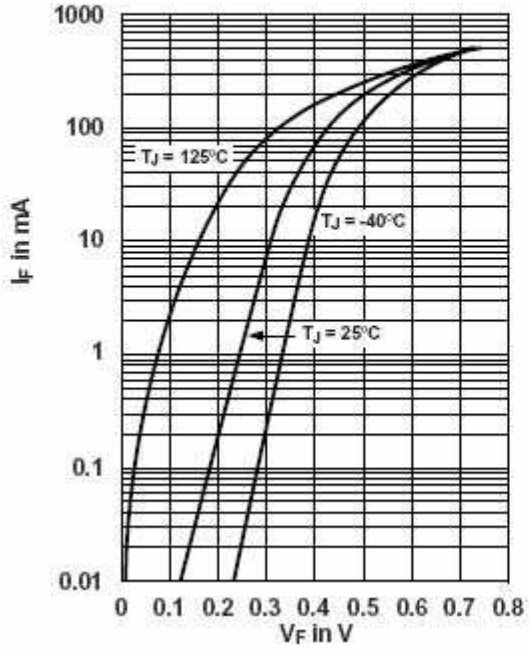
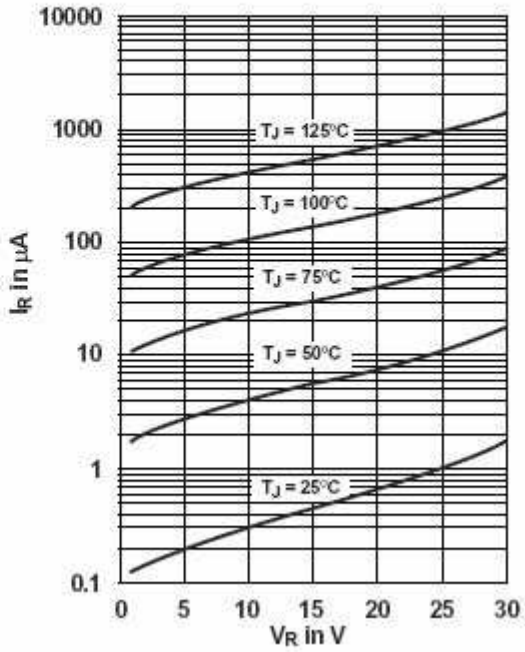
RATINGS AND CHARACTERISTIC CURVES

Forward Voltage Forward Current at Various Temperatures (Typical Values)



Typical Variation of Reverse Current at Various Temperatures



Typical Capacitance °C vs. Reverse Applied Voltage V_R